EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	73728	(thin near4 layer) near8 (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:13
S2	1409	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and carrier and recombination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:13
S3	287	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:13
S4	49	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination) and (resist$4 near4 contact)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:16
S5	6	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination) and (resist$4 near4 contact) and (metal near4 alloy) and dop$4 near4 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/01 10:17
S6	22	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination) and (resist$4 near4 contact) and (metal near4 alloy) and dop$4 near4 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:21

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S7	9	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination) and (resist$4 near4 contact) and (metal near4 alloy) and dop$4 near4 (substrate or semiconductor or wafer) and treat$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 10:22
S8	20	(thin near4 layer) near8 (semiconductor or substrate or wafer) and metal and (carrier near4 recombination) and (resist$4 near4 contact) and (metal near4 alloy) and dop$4 near4 (substrate or semiconductor or wafer) and (treat$4 or anneal or heat or thermal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:23
S9	99486	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:26
S10	1932	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:27
S11	250	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and recombination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:27
S12	837	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:27

S13	218	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:28
S14	214	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:29
S15	152	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:29
S16	105	(metal near4 (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4 and (thin near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:35
S17	70	(metal near (substrate or semiconductor or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4 and (thin near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:38
S18	42	(metal near (substrate or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion") and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4 and (thin near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:44

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S19	46	(metal near (substrate or wafer)) and (bond$4 or "thermal compression" or "molecular adhesion" or solder$4) and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4 and (thin near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:46
S20	22	(metal near (substrate or wafer)) and ("thermal compression" or "molecular adhesion" or solder$4) and (active near4 part) and (carrier naer4 recombination) and (metal near4 alloy) and (treat$4 or heat$4 or thermal$4 or anneal$4) and dop$4 and (thin near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 11:47